

**Pb Free Plating Product**

## MBRF2040CT thru MBRF20250CT



20.0 Amperes Insulated Dual Common Cathode Schottky Half Bridge Rectifiers

### Features

- ★ Latest MBR matured technology with high reliability
- ★ Low forward voltage drop
- ★ High current capability
- ★ Low reverse leakage current
- ★ High surge current capability

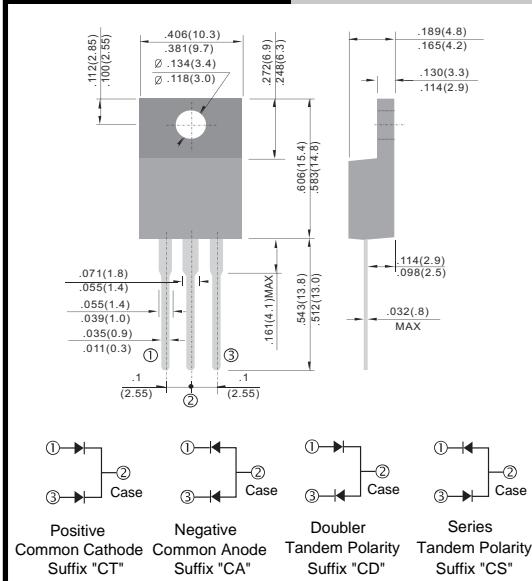
### Application

- ★ Automotive Inverters and Solar Inverters
- ★ Plating Power Supply, SMPS, EPS and UPS
- ★ Car Audio Amplifiers and Sound Device Systems

### Mechanical Data

- ★ Case: Fully Isolated Molding TO-220F Full Plastic Pak
- ★ Epoxy: UL 94V-0 rate flame retardant
- ★ Terminals: Solderable per MIL-STD-202 method 208
- ★ Polarity: As marked on diode body
- ★ Mounting position: Any
- ★ Weight: 2.2 gram approximately

### ITO-220AB



## Maximum Ratings And Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Parameter	Symbol	MBRF2040CT	MBRF2060CT	MBRF20100CT	MBRF20150CT	MBRF20200CT	MBRF20250CT	Unit
Body Marking		MBRF2040CT	MBRF2060CT	MBRF20100CT	MBRF20150CT	MBRF20200CT	MBRF20250CT	
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	40	60	100	150	200	250	V
Maximum RMS Voltage	V <sub>RMS</sub>	28	42	70	105	140	175	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	40	60	100	150	200	250	V
Maximum Forward Voltage @10A, T <sub>A</sub> =25°C @10A, T <sub>A</sub> =125°C @20A, T <sub>A</sub> =25°C	V <sub>F</sub>	0.70 0.57 0.84	0.79 0.70 0.95	0.81 0.71 0.95	0.87 0.77 1.0	0.90 0.80 1.0	0.95 0.85 -	V
Operating Temperature	T <sub>J</sub>				-50 ~ +150			°C

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward Rectified Current	See Fig.1	I <sub>0</sub>			20	A
Forward Surge Current	8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>			150	A
Reverse Current	V <sub>R</sub> =V <sub>RRM</sub> , T <sub>A</sub> =25°C V <sub>R</sub> =V <sub>RRM</sub> , T <sub>A</sub> =125°C	I <sub>R</sub>			0.1 10	mA
Thermal Resistance	Junction to ambient	R <sub>θJA</sub>	30			°C/W
Diode Junction Capacitance	f=1MHz and applied 4V DC reverse voltage	C <sub>J</sub>	150			pF
Storage Temperature		T <sub>STG</sub>	-50		+150	°C

## Rated and Characteristic Curve

Fig. 1 - Forward Current Derating Curve

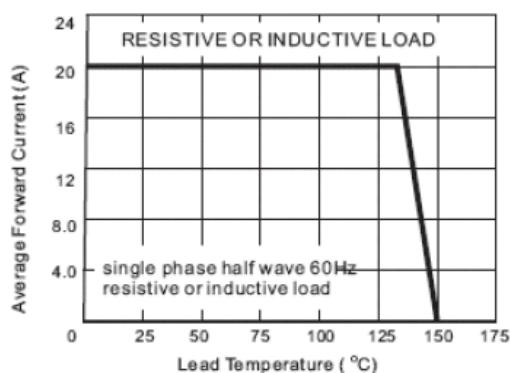


Fig. 3.1 - Typical Instantaneous Forward Characteristics

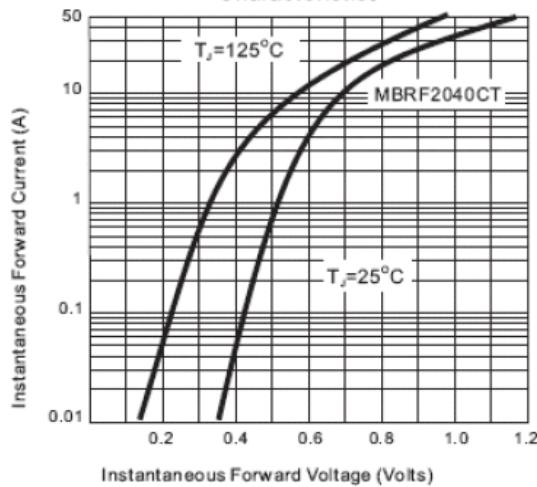


Fig. 3.3 - Typical Instantaneous Forward Characteristics

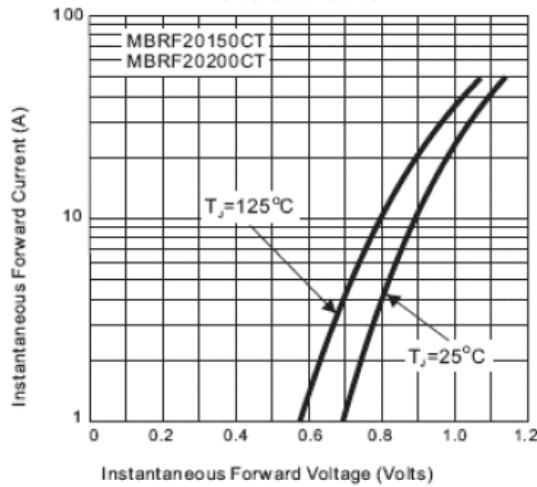


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

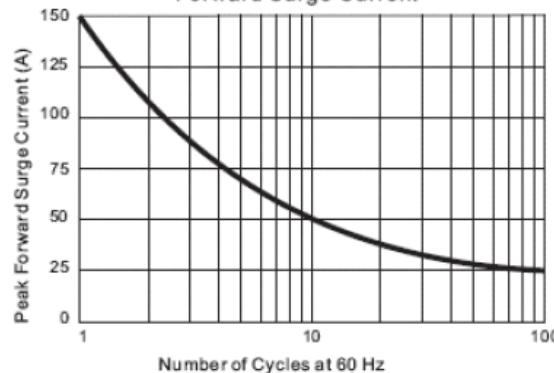


Fig. 3.2 - Typical Instantaneous Forward Characteristics

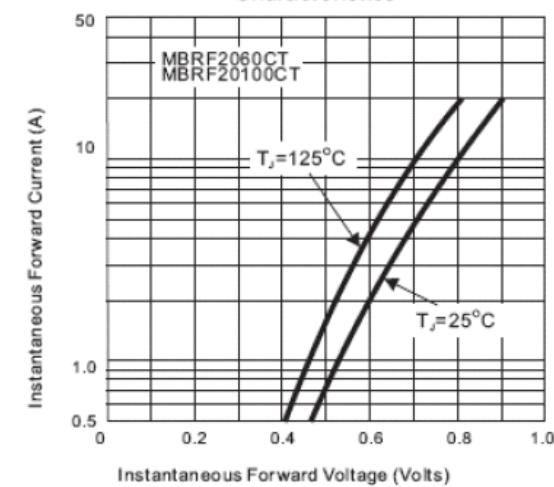


Fig. 4 - Typical Reverse Characteristics

